

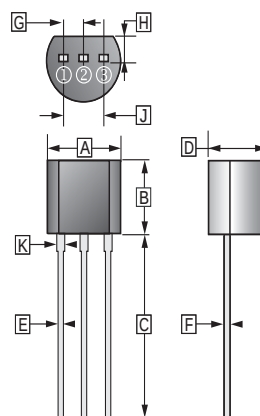
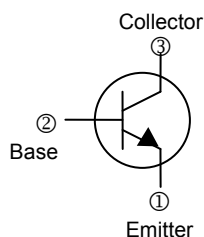
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Voltage Transistors
- Complement of the 2N6520

TO-92



① Emitter
② Base
③ Collector

REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	350	V
Collector to Emitter Voltage	V_{CEO}	350	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C	0.625	W
Thermal resistance, Junction to ambient	$R_{\theta JA}$	200	$^\circ\text{C} / \text{W}$
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	350	-	-	V	$I_C=0.1\text{mA}, I_E=0$
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	350	-	-	V	$I_C=1\text{mA}, I_B=0$
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	6	-	-	V	$I_E=0.01\text{mA}, I_C=0$
Collector Cut-Off Current	I_{CBO}	-	-	0.05	μA	$V_{CB}=250\text{V}, I_E=0$
Emitter Cut-Off Current	I_{EBO}	-	-	0.05	μA	$V_{EB}=5\text{V}, I_C=0$
DC Current Gain	$h_{FE(1)}^*$	20	-	-		$V_{CE}=10\text{V}, I_C=1\text{mA}$
	$h_{FE(2)}^*$	30	-	-		$V_{CE}=10\text{V}, I_C=10\text{mA}$
	$h_{FE(3)}^*$	30	-	200		$V_{CE}=10\text{V}, I_C=30\text{mA}$
	$h_{FE(4)}^*$	20	-	200		$V_{CE}=10\text{V}, I_C=50\text{mA}$
	$h_{FE(5)}^*$	15	-	-		$V_{CE}=10\text{V}, I_C=100\text{mA}$
Collector to Emitter Saturation Voltage	$V_{CE(sat)}^*$	-	-	0.3	V	$I_C=10\text{mA}, I_B=1\text{mA}$
		-	-	1.0		$I_C=50\text{mA}, I_B=5\text{mA}$
Base to Emitter Saturation Voltage	$V_{BE(sat)}^*$	-	-	0.75	V	$I_C=10\text{mA}, I_B=1\text{mA}$
		-	-	0.85		$I_C=20\text{mA}, I_B=2\text{mA}$
		-	-	0.9		$I_C=30\text{mA}, I_B=3\text{mA}$
Base to Emitter Voltage	V_{BE}^*	-	-	2	V	$V_{CE}=10\text{V}, I_C=100\text{mA}$
Collector to Base Capacitance	C_{ob}	-	-	6	pF	$V_{CB}=20\text{V}, I_E=0\text{A}, f=1\text{MHz}$
Transition Frequency	f_T^*	40	-	200	MHz	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=20\text{MHz}$

*Pulse test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$